

Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(Use as many sheets as necessary)</i>		Complete if Known Application Number   10/789,882 Filing Date   February 27, 2004 First Named Inventor   Farrar, Paul Group Art Unit   2818 Examiner Name   Unknown - D. NGUYEN	
		Attorney Docket No: 303.673US3	
Sheet 1 of 1			

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		Application Number	Unknown 10/789,882
		Filing Date	Even Date Herewith 02/27/04
		First Named Inventor	Farrar, Paul
		Group Art Unit	Unknown 2818
		Examiner Name	Unknown D. NGUYEN
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		Examiner Name	Unknown D. NGUYEN			
Sheet 2 of 10		Attorney Docket No: 303.673US3				

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		Group Art Unit	Unknown 2818
		Examiner Name	Unknown D. NGUYEN
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**INFORMATION DISCLOSURE  
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First Named Inventor	Farrar, Paul	
Group Art Unit	Unknown	2818
Examiner Name	Unknown	D. NGUYEN

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	US-6,420,262	07/16/2002	Farrar, Paul A.	438	652	01/18/2000
dlm	US-6,426,289	07/30/2002	Farrar, P A.			
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		Application Number	Unknown → 10/789, 882
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		Group Art Unit	Unknown 2818
		Examiner Name	Unknown D. NGUYEN
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